

L2*570/660/805/940/975-35Q96-I Multi-wavelength LED

L2X570/660/805/940-35Q96-I consists of 6chips of InGaAlAs'(570nm), AlGaAs'(660, 805nm)and GaAs'(940, 975nm) LED mounted with AlN heat sink pedestal on TO-5 stem and sealed with an flat glass can.

†Specifications

1)Product No.	Multi-wavelength LED Lamp	(3)Chip numbers	570nm-2pcs, 660-975nm-1pcs
2)type No.	L2*570/660/805/940/975-35Q96-I	4)wire connection	Cathode common
3)Chip		4)Package	
(1)Chip material	InGaAlP GaAlAs GaAs	(1)stem type	TO-5 8pin type stem
(2)Peak wavelength	570,660, 805, 940,975nm	(2)Lens	Ø5.9mm Flat glass

†Absolute Maximum Ratings Ta=25 °C

Item	Symbol	Maximum Rated Value					Unit
		570	660	805	940	975	
Power Dissipation	PD	130	120	170	140	130	mW
Forward Current	IF	50	50	100	100	100	mA
Pulse Forward Current	IFP	200	200	500	1000	1000	mA
Reverse Voltage	VR	5					V
Operating Temperature e	TOPR	-20~+80					°C
Storage Temperature	TSTG	-30~+100					°C
Soldering Temperature	TSOL	240					°C

†Electro-Optical Characteristics(Ta=25 °C)

Item		Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	570nm	VF	IF=20mA		2.25	2.50	V
	660nm				1.90	2.30	
	805nm				1.50	1.70	
	940nm				1.25	1.40	
	975nm				1.20	1.40	
Reverse Current		IR	VR=5V			10	uA
Total Radiation Power	570nm	Po	IF=20mA		0.6		mW
	660nm				2.9		
	805nm				3.5		
	940nm				2.5		
	975nm				0.9		
Peak Wavelength	570nm	ëP	IF=20mA	567	570	576	nm
	660nm			650	660	670	
	805nm			795	805	815	
	940nm			935	940	955	
	975nm			960	975	980	
Half Width	570nm	ë8	IF=20mA		15		nm
	660nm				20		
	805nm				30		
	940nm				45		
	975nm				55		

Outer Dimension

